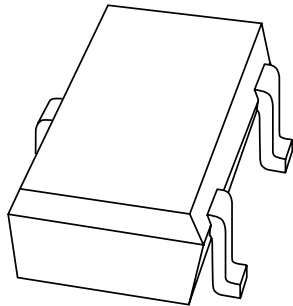


# DATA SHEET



## **PMST4401** NPN switching transistor

Product data sheet  
Supersedes data of 1997 May 07

1999 Apr 22

# NPN switching transistor

# PMST4401

### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

### APPLICATIONS

- General purpose switching and linear amplification, especially in portable equipment.

### DESCRIPTION

NPN switching transistor in a SOT323 plastic package.  
PNP complement: PMST4403.

### MARKING

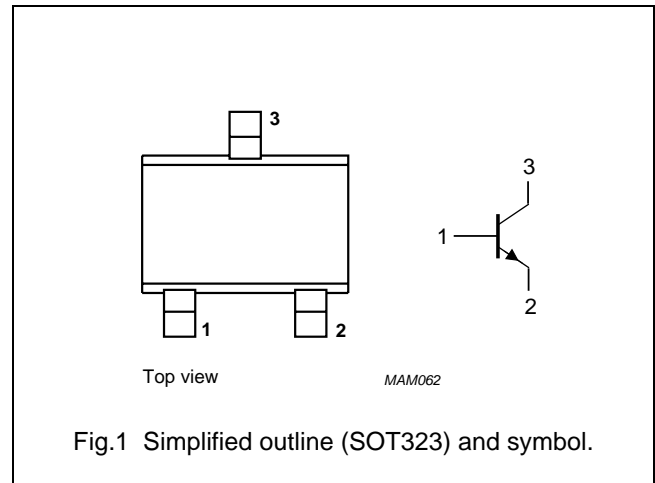
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMST4401	*2X

### Note

- \* = - : Made in Hong Kong.  
\* = t : Made in Malaysia.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current (DC)		-	600	mA
I <sub>CM</sub>	peak collector current		-	600	mA
I <sub>BM</sub>	peak base current		-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN switching transistor

## PMST4401

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	50	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 6\text{ V}$	–	50	nA
$h_{FE}$	DC current gain	$V_{CE} = 1\text{ V}$ ; (see Fig.2)			
		$I_C = 0.1\text{ mA}$	20	–	
		$I_C = 1\text{ mA}$	40	–	
		$I_C = 10\text{ mA}$	80	–	
		$I_C = 150\text{ mA}$ ; note 1	100	300	
	DC current gain	$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$ ; note 1	40	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$ ; note 1	–	400	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$ ; note 1	–	750	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$ ; note 1	–	950	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$ ; note 1	–	1.2	V
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	8	pF
$C_e$	emitter capacitance	$I_E = i_e = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	30	pF
$f_T$	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	250	–	MHz
<b>Switching times (between 10% and 90% levels); (see Fig.3)</b>					
$t_{on}$	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA};$ $I_{Boff} = -15\text{ mA}$	–	35	ns
$t_d$	delay time		–	15	ns
$t_r$	rise time		–	20	ns
$t_{off}$	turn-off time		–	250	ns
$t_s$	storage time		–	200	ns
$t_f$	fall time		–	60	ns

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

NPN switching transistor

PMST4401

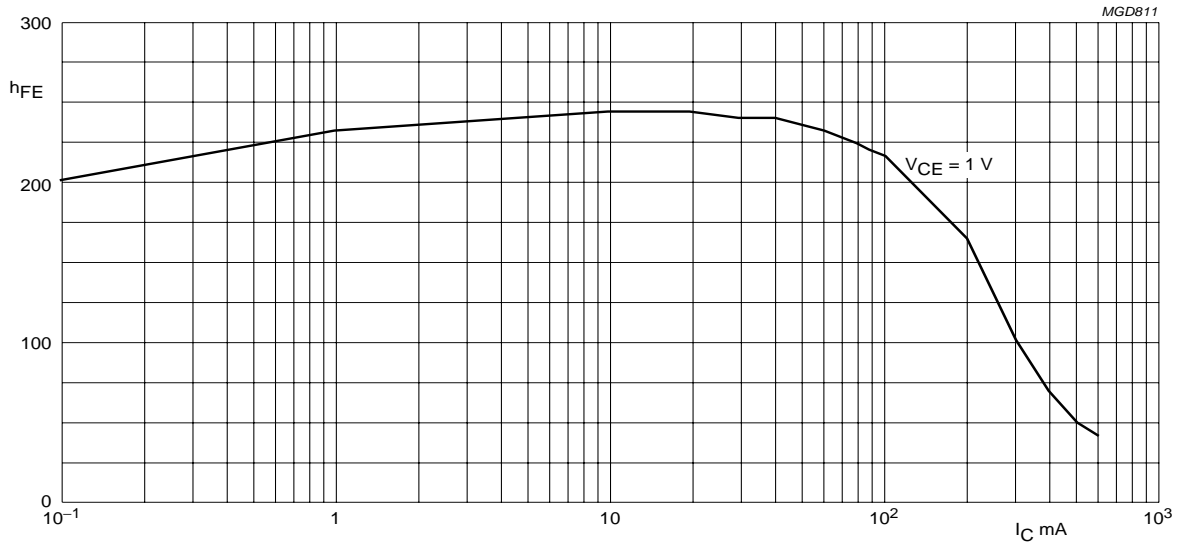
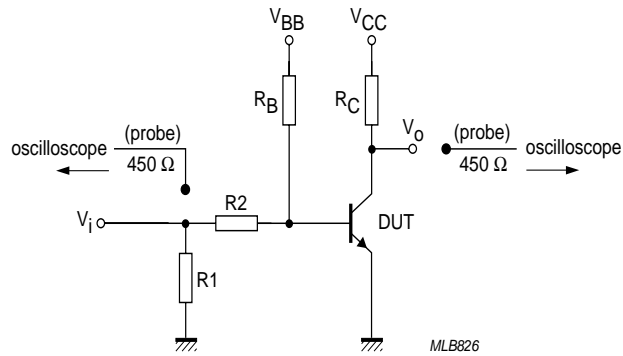


Fig.2 DC current gain; typical values.



$V_i = 9.5 \text{ V}$ ;  $T = 500 \mu\text{s}$ ;  $t_p = 10 \mu\text{s}$ ;  $t_r = t_f \leq 3 \text{ ns}$ .  
 $R_1 = 68 \Omega$ ;  $R_2 = 325 \Omega$ ;  $R_B = 325 \Omega$ ;  $R_C = 160 \Omega$ .  
 $V_{BB} = -3.5 \text{ V}$ ;  $V_{CC} = 29.5 \text{ V}$ .  
 Oscilloscope: input impedance  $Z_i = 50 \Omega$ .

Fig.3 Test circuit for switching times.

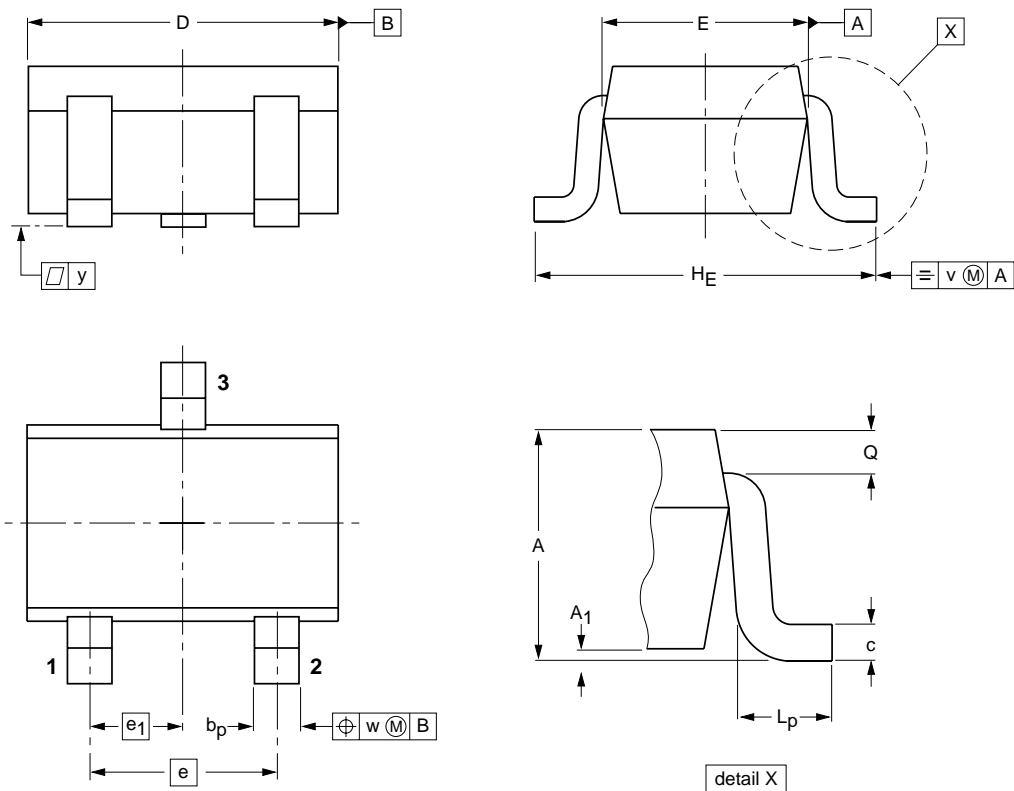
NPN switching transistor

PMST4401

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

# NPN switching transistor

PMST4401

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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